

Amendments to the Specification

Please replace the paragraph beginning on page 13, line 29, with the following rewritten paragraph:

Furthermore, the application of the ozonated substance may be conducted in a variety of manners. For example, the ozonated substance may be applied in the form of a liquid or a vapor. As such, the ozonated substance may be applied at a variety of temperatures. For instance, the ozonated substance may be applied at temperatures ranging from approximately 10 °C and 1000 °C. In a preferred embodiment, the ozonated substance may be applied at a temperature between approximately 20 °C and 25 °C. In some embodiments, the ozonated substance may be applied at the substantially the same temperature of the transfer chamber connected to the oxidation chamber. In this manner, the temperature differential during the process of transferring the semiconductor topography between the oxidation process and the subsequent nitride deposition process may be minimized. In general, the application of the ozonated substance may advantageously form an oxide film, which is of higher quality than films formed after conventional wet-cleaning techniques. For example, the application of an ozonated substance may produce an oxide film that is more dense ~~that than~~ oxide layers grown using conventional methods. In addition or alternatively, an oxide film formed from an ozonated substance may have fewer defects than an oxide layer grown from conventional techniques. In particular, an oxide film formed from an ozonated substance may include less pinholes and voids than an oxide layer grown from conventional methods.